

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(@ad<"2002") and (chip or die) and (annular near ring)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 09:51
L2	0	(@ad<"2002") and (chip or die) and ((insulation or insulating) near ring)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 10:29
L3	3187	(@ad<"20020125") and (chip or die) and (annular near ring)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 09:52
L4	202	L3 and pole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 09:55
L5	905	L3 and (pole or cap or lid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 09:53
L6	1	("6781227").PN.	USPAT	OR	OFF	2005/03/03 09:55
L7	5	("3599057" "3831067" "4008486" "5278434" "5641976").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/03 09:56
L8	6	("5641976").URPN.	USPAT	OR	OFF	2005/03/03 09:56
L9	6	("5641976").URPN.	USPAT	OR	OFF	2005/03/03 10:00
L10	5	("4667219" "5221851" "5297001" "5641976" "5705853").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/03 10:00
L11	16	("3831067").URPN.	USPAT	OR	OFF	2005/03/03 10:14
L12	0	(@ad<"2002") and (chip or die or semiconducotr or anode) and (ring) and control	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:52

L13	56416	(@ad<"20020125") and (chip or die or semiconductor or anode) and ring and control	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 10:38
L14	75282	(@ad<"20020125") and (chip or die or semiconductor or anode) and ring and control	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:34
L15	10364	L14 and flange	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 10:41
L16	985	L15 and (ring with (terminal or lead or electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 10:42
L17	347007	(@ad<"20020125") and 257/688. ccls. and ring and control anode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:35
L18	34	(@ad<"20020125") and 257/688. ccls. and ring and control and (anode or thyristor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:41
L19	6	(@ad<"20020125") and 257/692. ccls. and ring and (control or gate) and (anode or thyristor) and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:42
L20	7	(@ad<"20020125") and 257/724. ccls. and ring and (control or gate) and (anode or thyristor) and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:43

L21	1	(@ad<"20020125") and 257/584. ccls. and ring and (control or gate) and (anode or thyristor) and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:44
L22	0	(@ad<"20020125") and 257/696. ccls. and ring and (control or gate) and (anode or thyristor) and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:44
L23	21	(@ad<"20020125") and 257/181. ccls. and ring and (control or gate) and (anode or thyristor) and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:50
L24	11083	(@ad<"20020125") and ring and (control or gate) and (anode or thyristor) and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:51
L25	11060	L24 not L4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:51
L26	4656	L24 and (chip or die or semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:53
L27	2754	L26 and (therethrough or insert or opening or groove)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:54
L28	1988	L27 and (compression or compress or press or pressure or fitted)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:55

L29	766	L27 not L28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:55
L30	1902	L26 not L27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/03 11:55